

# An Ambient RF Energy Harvester With Integrated Power Management Unit

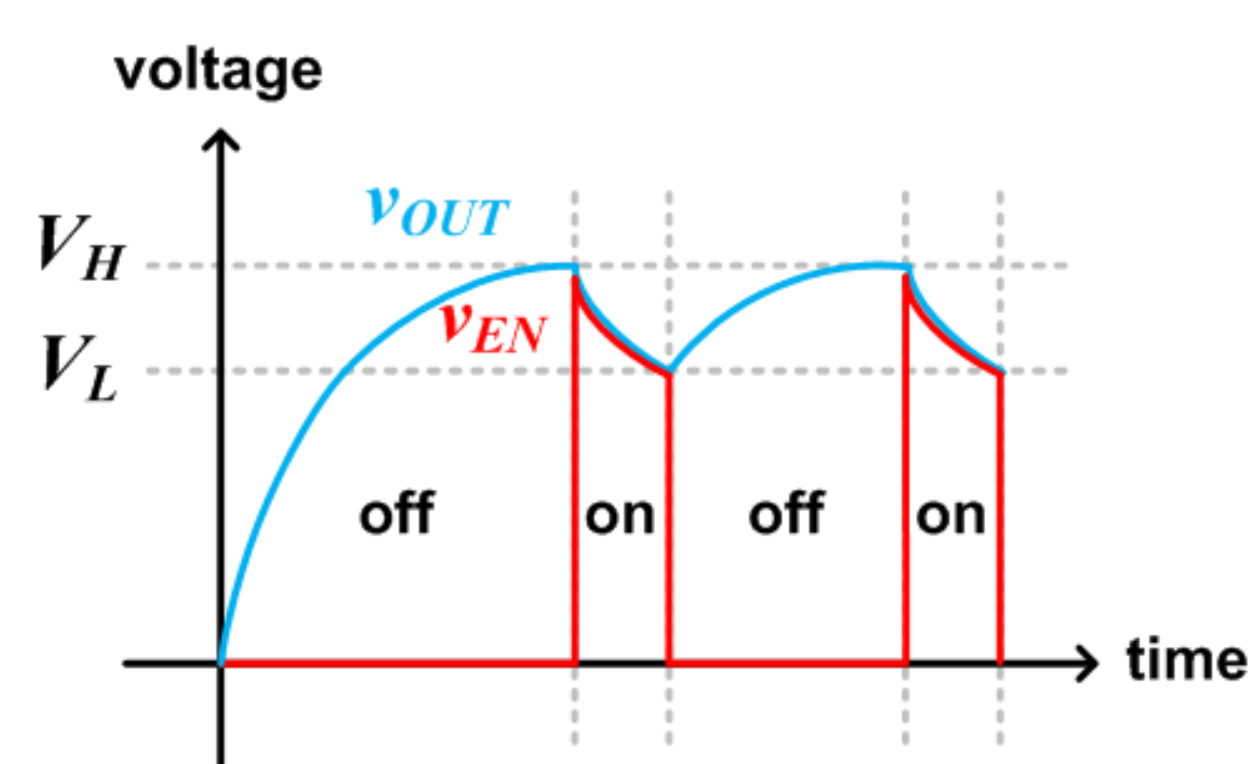
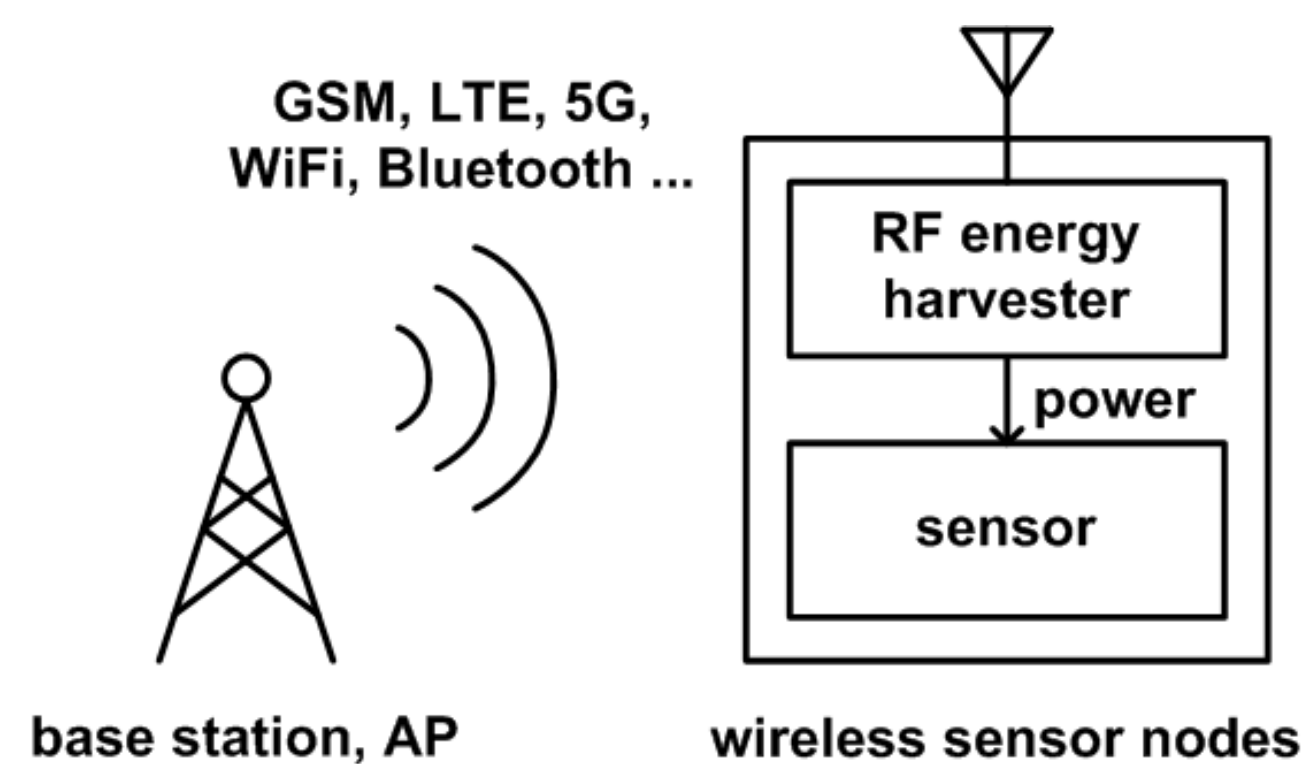
Yoomi Park, Hyeonsoo Seung and Sangjin Byun

Department of Electronics and Electrical Engineering, Dongguk University

## INTRODUCTION

### Ambient RF Energy Harvester

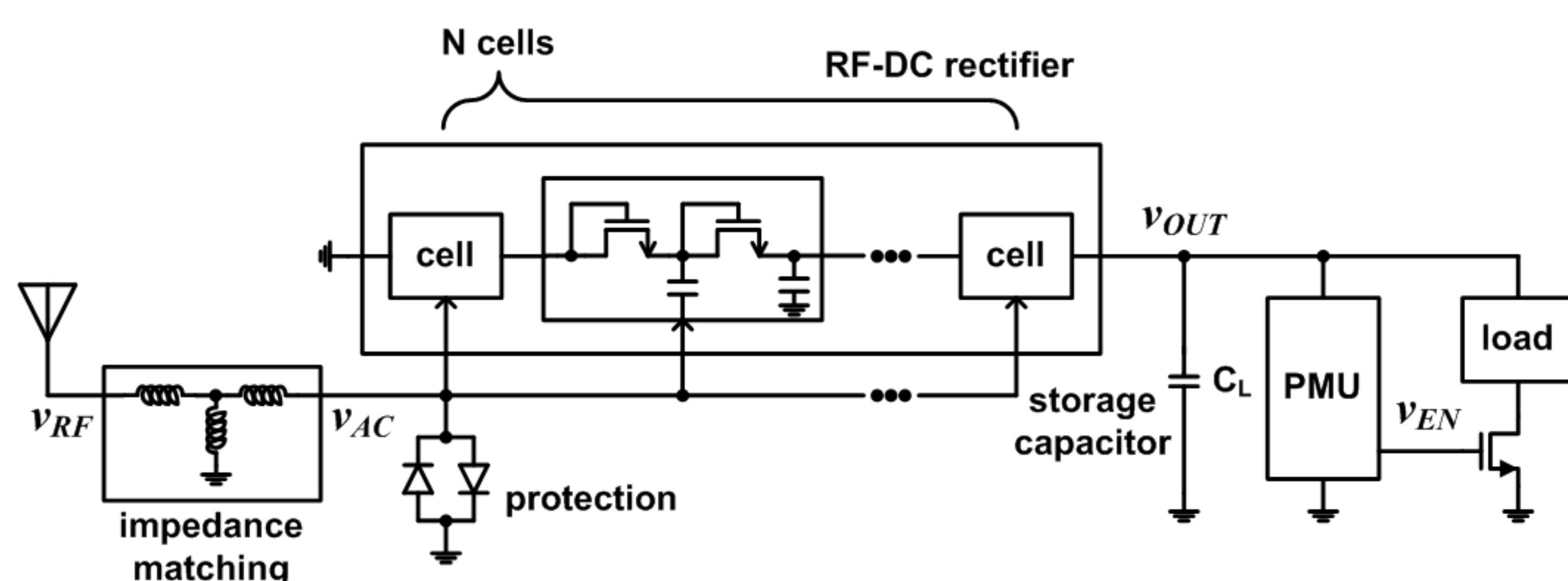
### Duty-Cycled Operation



- For ambient RF energy harvesters, the available power from ambient RF signals is typically lower than the power required for sensing and data transmission
- Thus, it should supply power to the load in duty cycle to harvest enough energy

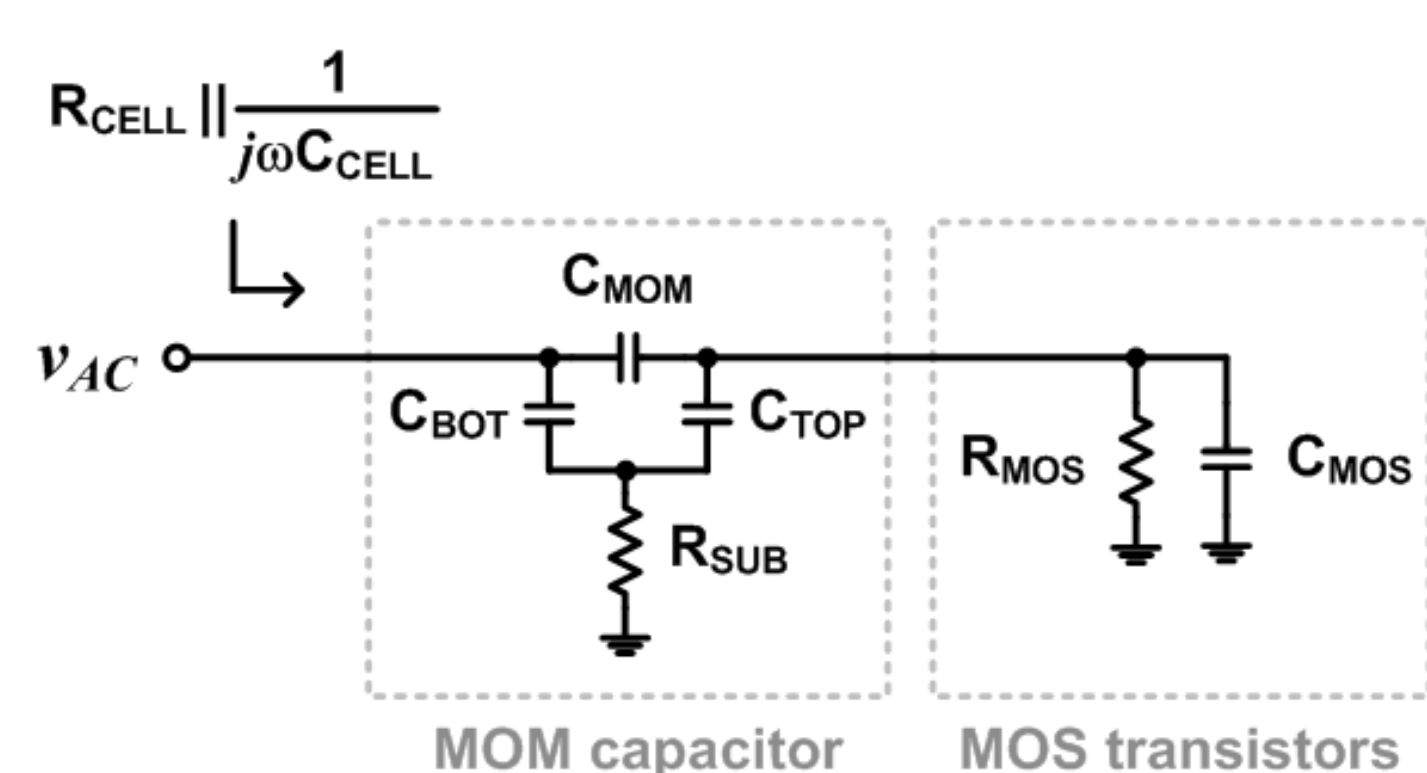
## IMPLEMENTATION

### Architecture of the Ambient RF Energy Harvester



- Impedance matching network with high quality factor ( $> 70$ )
- RF-DC rectifier composed of N rectifier cells for high input sensitivity ( $> -40\text{dBm}$ )
- Power management unit operating with ultra low power consumption ( $< 1\text{nW}$ )

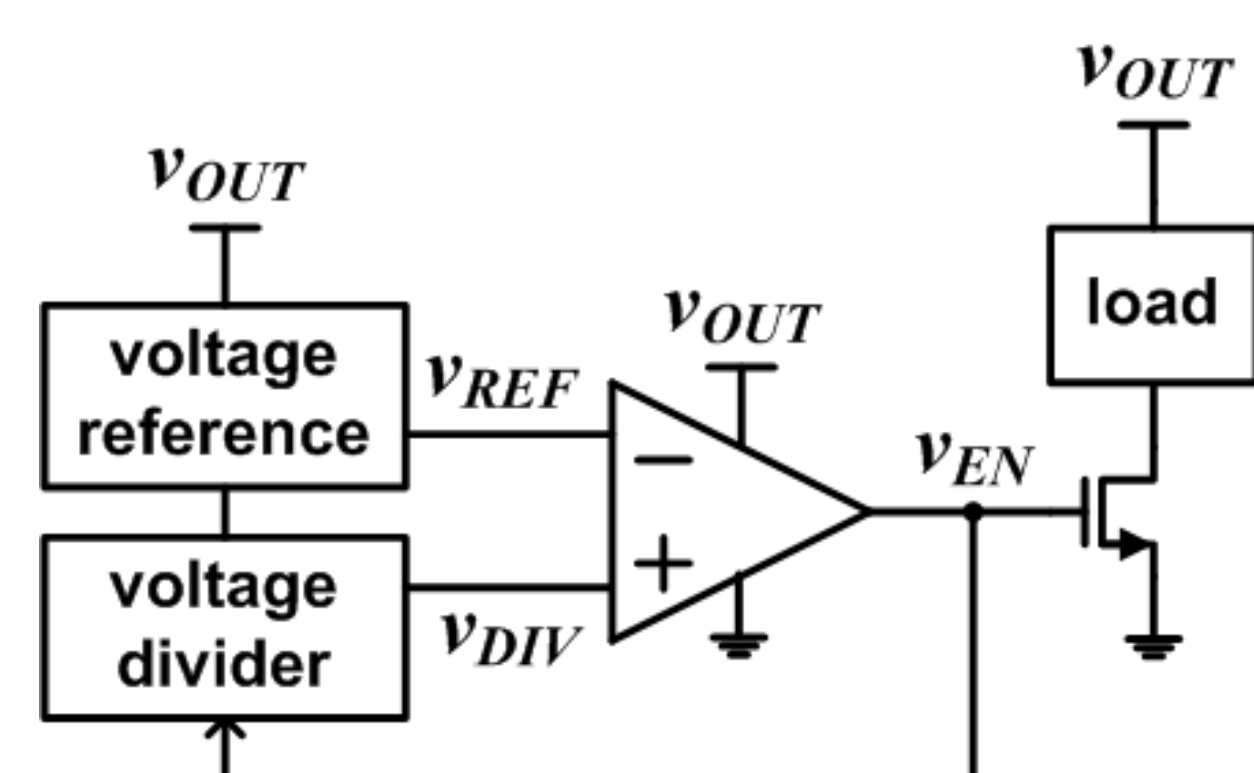
### RF-DC Rectifier



$$R_{CELL} \approx R_{MOS} || R_{SUB} (1 + Q^2)$$

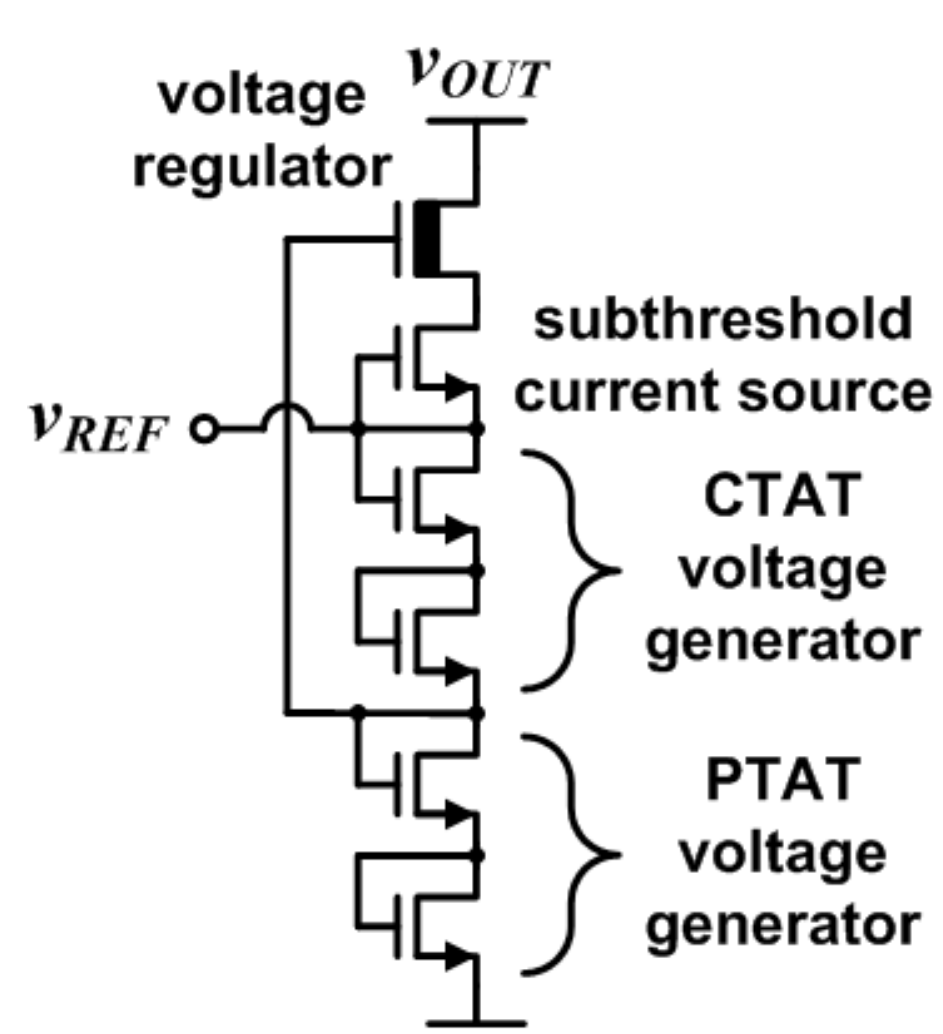
$$\text{where } Q = \frac{1}{\omega(C_{TOP} + C_{BOT})R_{SUB}}$$

### Power Management Unit



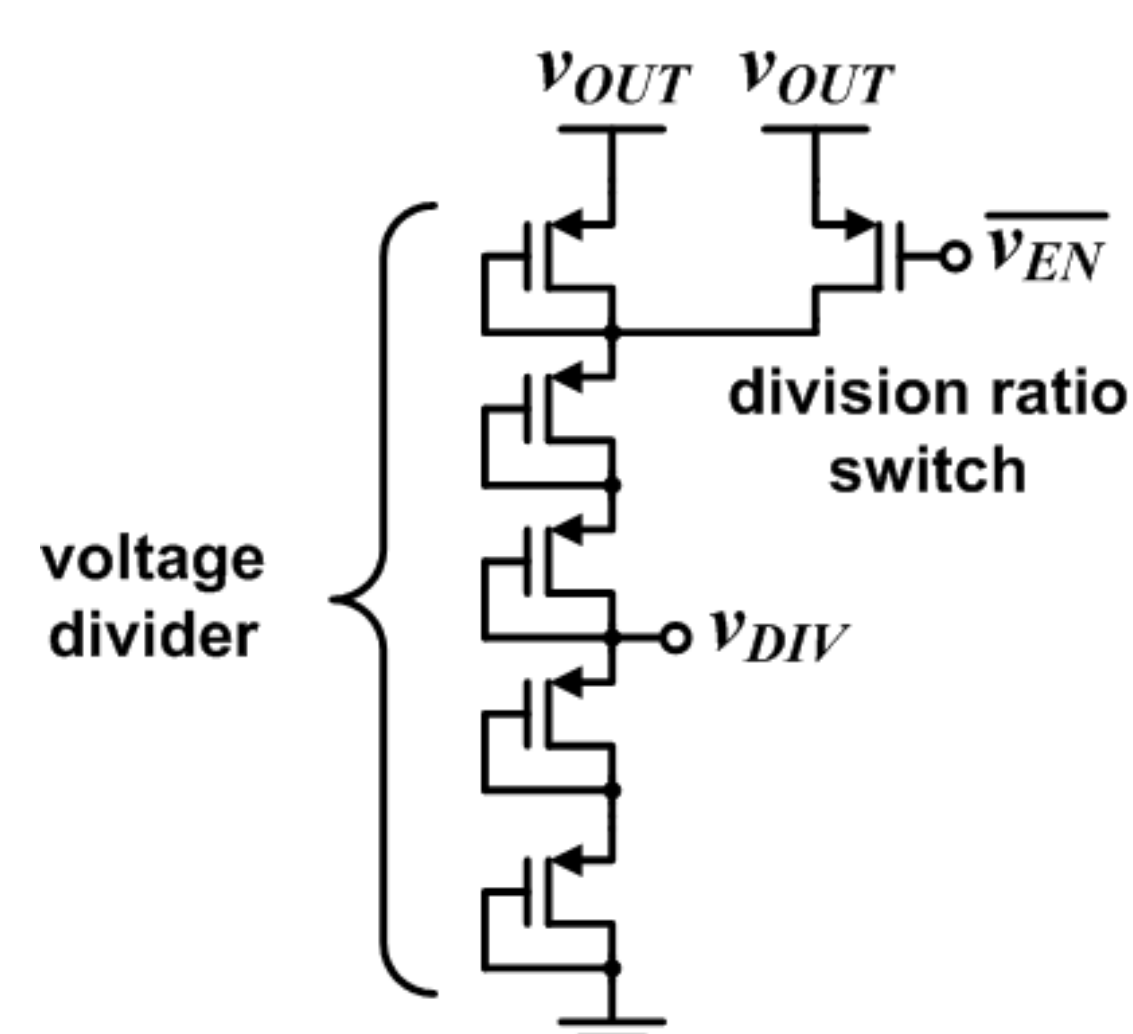
$v_{EN}$  goes high when  $v_{DIV} > v_{REF}$  and voltage divider makes hysteresis

### Voltage Reference



Temperature variation is compensated by using different types of transistors

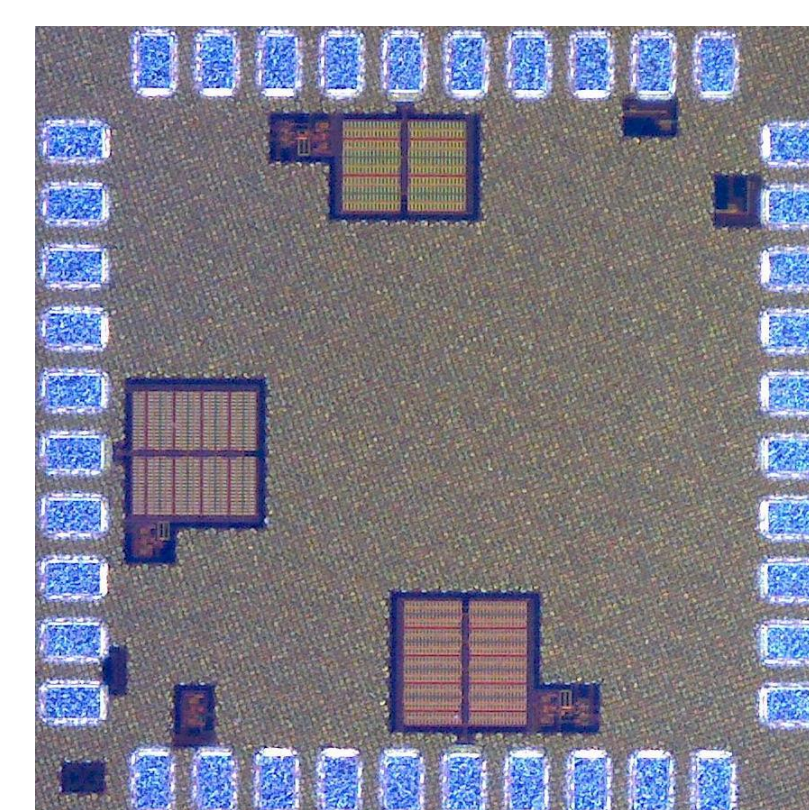
### Voltage Divider



Voltage division ratio is changed by using the load enable signal

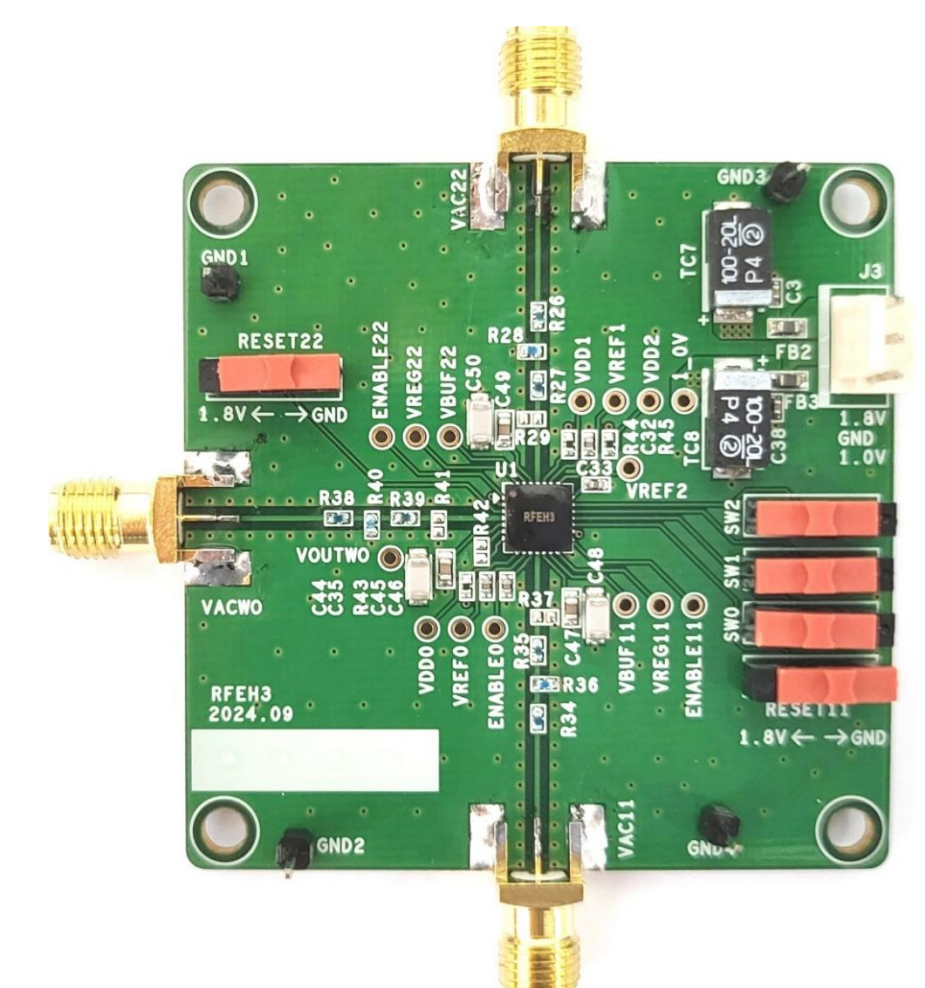
## MEASUREMENT

### Die Photo



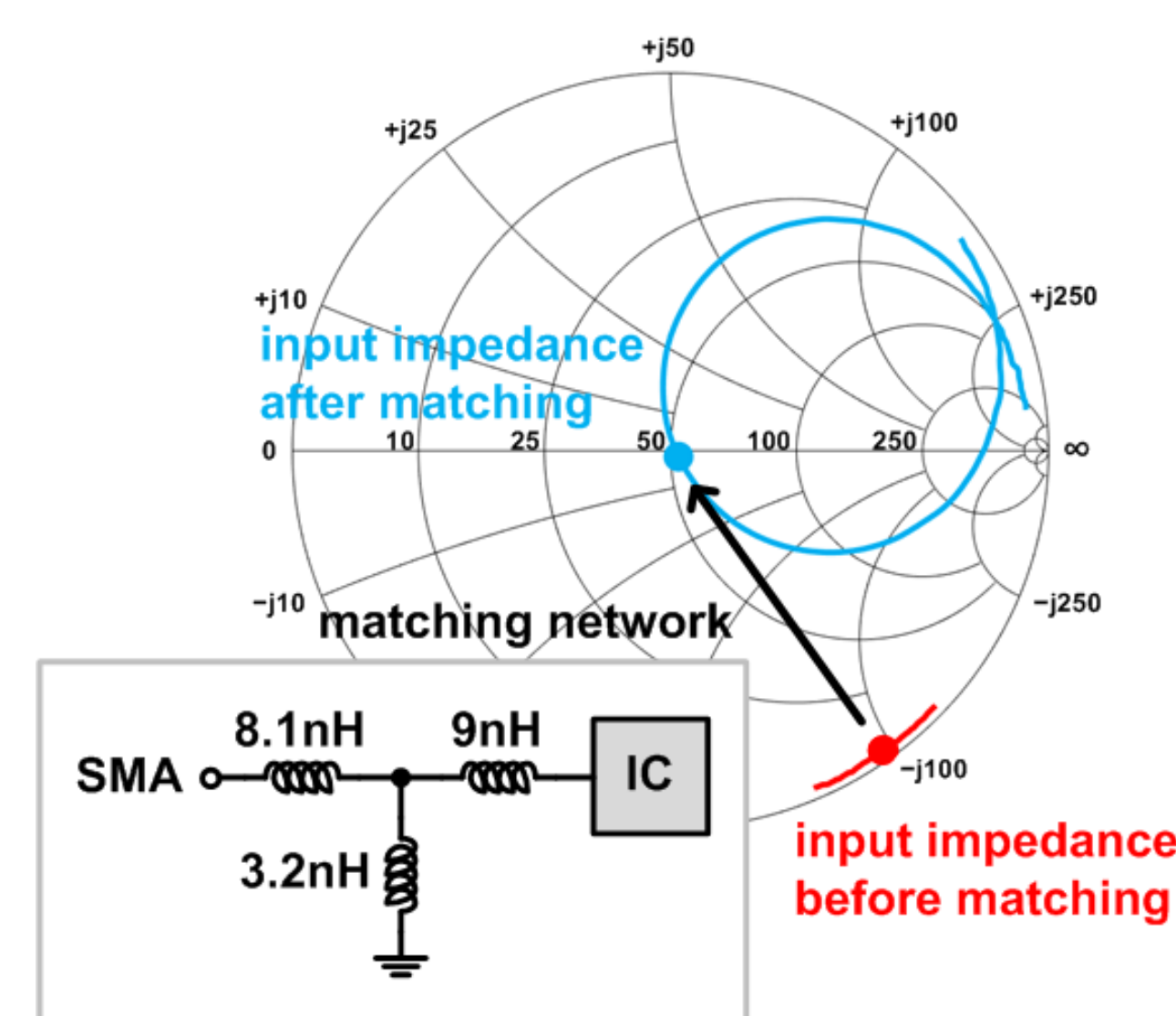
Samsung 28nm 1P11M CMOS  
Active area: 217um x 203um

### Test Board



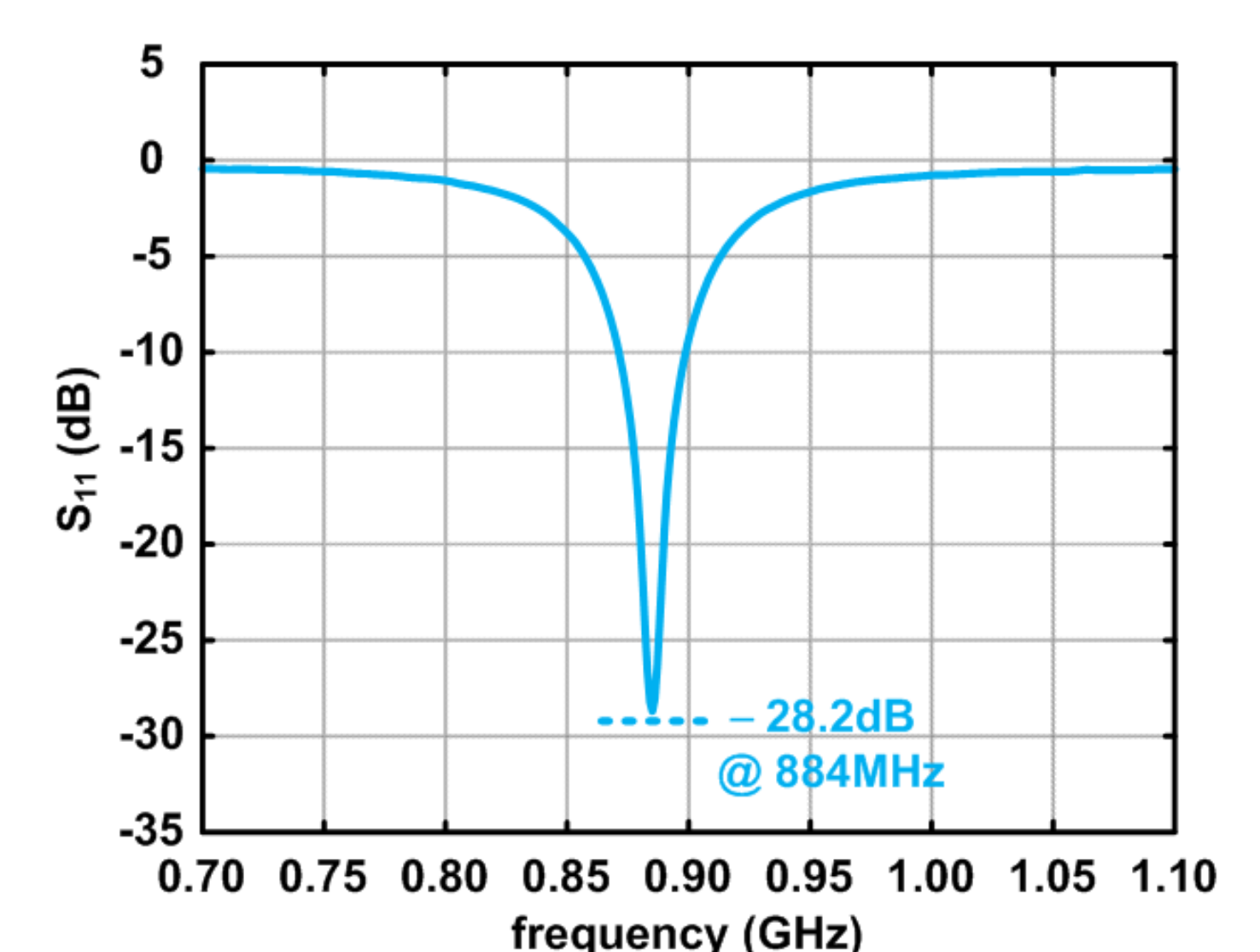
28 pin QFN 5mm x 5mm  
4 layer FR4 PCB

### Impedance Matching Network



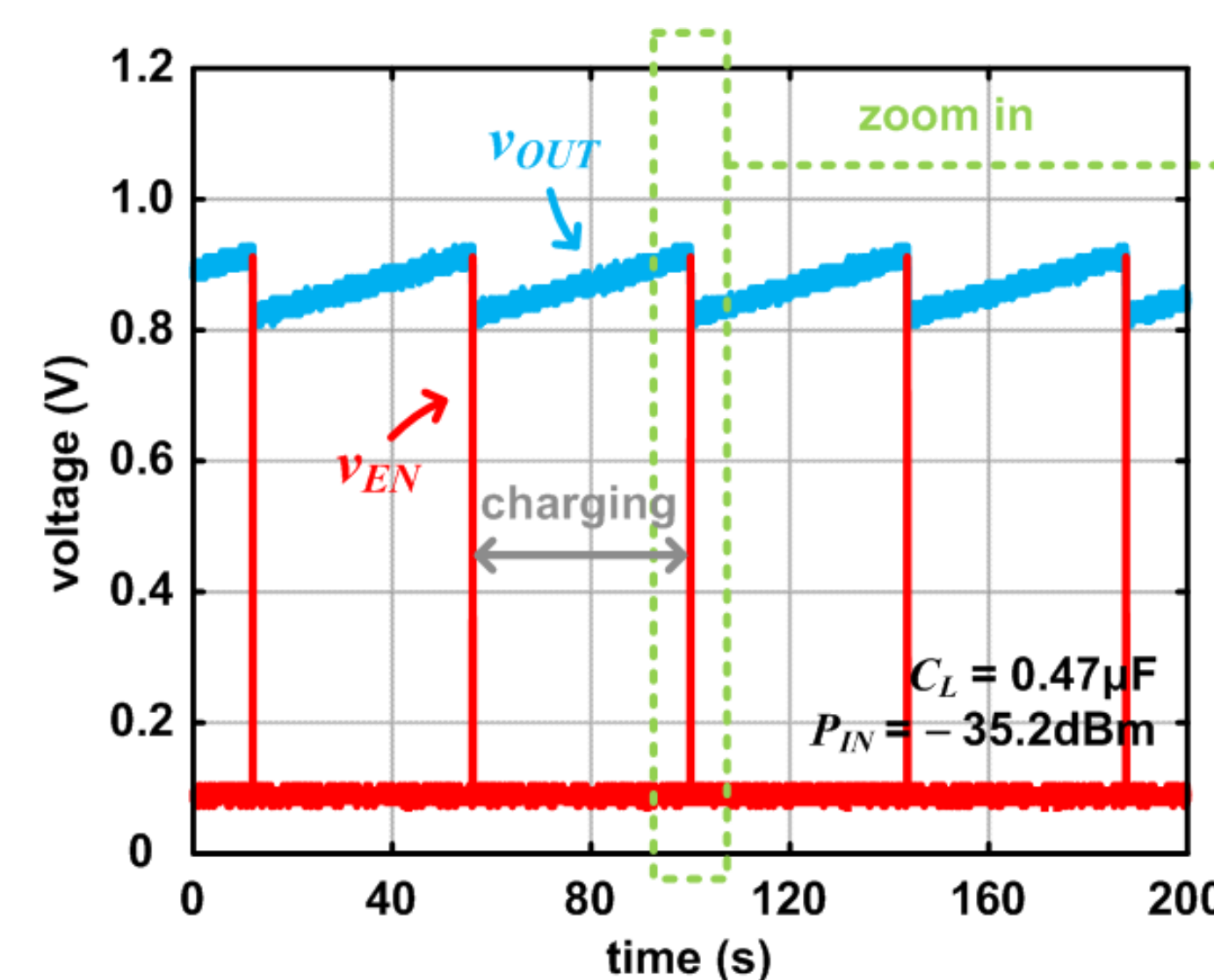
Passive gain = 8.6V/V @  $-40\text{dBm}$

### Scattering Parameter

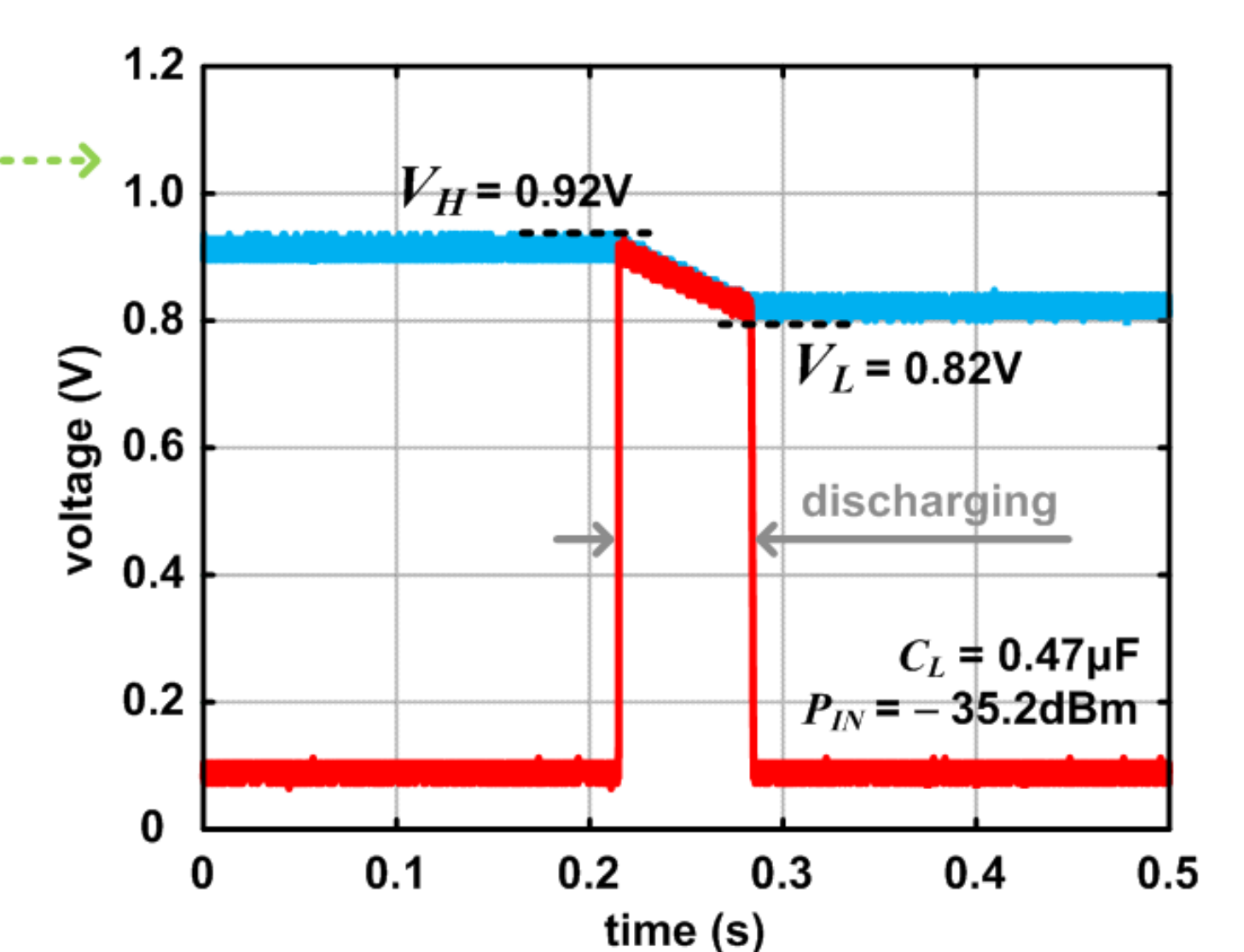


$-10\text{dB}$  bandwidth = 27.5MHz

### Transient Waveform of the Output Voltage



Charging time = 43.7s



Discharging time = 68.3ms @  $1\text{M}\Omega$

## CONCLUSION

### Performance Summary

	TMTT 21	TMTT 24	TCASI 24	TCASI 25	JSSC 25	this work
CMOS technology	130nm	28nm	28nm	55nm	65nm	28nm
RF frequency	0.868GHz	0.970GHz	0.884GHz	0.915GHz	2.4GHz	0.884GHz
active die area	0.047mm <sup>2</sup>	0.025mm <sup>2</sup>	0.09mm <sup>2</sup>	0.027mm <sup>2</sup>	0.7mm <sup>2</sup>	0.047mm <sup>2</sup>
self-powered PMU	X	X	X	O	O	O
output DC voltage	1V	1V	1V	1V	1.2V	0.87V
input sensitivity	-31dBm	-36.5dBm	-41.8dBm	-31dBm	-28.5dBm	-40.8dBm

- The ambient RF energy harvester has been fabricated in a 28nm CMOS process
- The self-powered PMU with the low current consumption has been integrated
- The implemented ambient RF energy harvester shows the high input power sensitivity of  $-40.8\text{dBm}$  for 0.87V while the power management unit is operating